

Application No.: 10/790,723**Docket No.: 2336-247****AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (original) A wafer level package comprising:
a device wafer having a micro device, and bonding pads connected to the micro device, which are formed at one surface of the device wafer;
via connectors extending from the bonding pads to the other surface of the device wafer;
external bonding pads formed at the other surface of the device wafer and adapted to be connected to the bonding pads through the via connectors, respectively; and
a cap structure bonded to one surface of the device wafer so as to allow the micro device to be insulated and hermetically sealed.
2. (original) The package as set forth in claim 1, wherein the cap structure has a cavity at a portion corresponding to the micro device.
3. (original) The package as set forth in claim 1, wherein the cap structure is a silicon wafer or glass wafer.
4. (original) The package as set forth in claim 1, further comprising:
a sealing member for bonding the cap structure to the device wafer.
5. (original) The package as set forth in claim 4, wherein:
the device wafer further has a peripheral metal pad formed around a perimeter of one

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surface thereof to be bonded to the cap structure; and

the sealing member is a metal material formed on the peripheral metal pad.

6. (original) The package as set forth in claim 4, wherein the sealing member is a glass frit.

7. (original) The package as set forth in claim 4, wherein the sealing member is a resin based adhesive.

8. (original) The package as set forth in claim 1, wherein the sealing is performed by an anodic bonding technique.

9. (original) The package as set forth in claim 1, wherein the cap structure has a dry film structure, the dry film structure having a well for receiving the micro device and bonding pads, and a passivation layer applied to an outer surface of the dry film structure.

10. (original) The package as set forth in claim 9, wherein the passivation layer is a material selected from among the group consisting of an epoxy resin, thermosetting resin, metal and photosensitive resin.

11. (withdrawn) A method [[for]] of manufacturing a wafer level package, said method comprising the steps of:

[[a]] preparing a device wafer in which a micro device, and bonding pads connected to the micro device are formed at one surface thereof;

[[b]] forming via connectors extending from the bonding pads to the other surface of the device wafer;

[[c]] bonding a cap structure to one surface of the device wafer so as to allow the micro

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device to be insulated and hermetically sealed; and

[[d]] forming external bonding pads at the other surface of the device wafer, the external bonding pads being connected to the bonding pads through the via connectors, respectively.

12-22. (canceled)

23. (new) The package as set forth in claim 1, further comprising a first cavity defined between the device wafer and the cap structure and a second cavity formed in the device wafer; wherein said micro device is positioned between said first and second cavities.

24. (new) The package as set forth in claim 1, wherein said micro device is a film bulk acoustic resonator (FBAR).

25. (new) The package as set forth in claim 1, further comprising a cavity defined between the device wafer and the cap structure; wherein said cavity is located corresponding to the micro device and the bonding pads; and wherein said bonding pads are completely located in said cavity.

26. (new) The package as set forth in claim 1, wherein said cap structure includes a depression having a bottom and side walls extending upwardly from the bottom, said depression defining together with said device wafer a cavity accommodating said micro device and bonding pads; and an entirety of each of the bonding pads is inwardly spaced from a closest one of said side walls.

27. (new) The package as set forth in claim 9, wherein the dry film structure is photosensitive.

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28. (new) The package as set forth in claim 9, wherein the passivation layer is formed on and covers

a top surface of the cap structure,

side surfaces of the cap structure, said side surfaces extending downwardly from the top surface toward the device wafer, and

outer peripheral portions of the surface of the device wafer that is bonded to the cap structure.

29. (new) A wafer level package, comprising:

a wafer having opposite upper and lower surfaces;

a micro device mounted on the upper surface of said wafer;

internal bonding pads positioned on the upper surface of said wafer and electrically connected to said micro device;

external bonding pads positioned on the lower surface of said wafer;

via connectors extending through said wafer from the upper surface to the lower surface and electrically connecting the internal bonding pads and the external bonding pads, respectively;

a cap structure bonded to the upper surface of said wafer and defining with said wafer a cavity in which said micro device is insulated and hermetically sealed;

wherein said internal bonding pads are completely located within said cavity.

30. (new) The package as set forth in claim 29, further comprising another cavity formed in the upper surface of said wafer;

wherein said micro device is positioned between said cavities and spans over said another cavity.

31. (new) The package as set forth in claim 30, wherein said micro device is a film

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bulk acoustic resonator (FBAR).

32. (new) The package as set forth in claim 29, wherein
said cap structure includes a depression having a top wall and side walls extending
downwardly from the top wall, said depression defining together with said wafer said cavity; and
an entirety of each of the internal bonding pads is inwardly spaced from a closest one of said
side walls.

33. (new) The package as set forth in claim 29, further comprising a passivation layer
that is formed on and covers
a top surface of said cap structure,
side surfaces of said cap structure, said side surfaces extending downwardly from the top
surface toward said wafer, and
outer peripheral portions of the upper surface of said wafer, said outer peripheral portions
surrounding a bonding region in which said cap structure and said wafer are sealingly bonded.